

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 7, line 25, of the specification, as follows:

--The plasma polymerizing etch deposits polymeric materials, typically in the form of  
5 layers (hereinafter "polymer layers"), on the walls of feature 210 during etching. The total  
thickness of the polymer layers deposited, e.g., from about ten nanometers to about 500  
nanometers, should be controlled such that the plasma polymerizing etchant species may still  
diffuse through the polymer layers and etch antireflective material 204. The thickness of the  
polymer layers deposited depends on the composition of the polymeric materials and whether the  
10 particular surface is subject to ion bombardment. For example, during etching of feature 210, the  
thickness of the polymer layers deposited during etching of radiation sensitive imaging layer 202  
is greater than the thickness of the polymer layers deposited during etching of antireflective  
material 204. In an exemplary embodiment, the total thickness of the polymer layers deposited  
during etching of radiation sensitive imaging layer 202 is up to about four nanometers at the  
15 thickest portion. For example, the total thickness of the polymer layers deposited during etching  
of radiation sensitive imaging layer 202 is between about one to about three nanometers at the  
thickest portion. The plasma polymerizing etch may be employed to reduce the critical  
dimensions of a feature by up to about 80 nanometers during etching of the antireflective  
material.--